

Deposition method for compound semiconductor forming device

Deposition method for compound semiconductor forming device

Patent Number: ☐ US5429068
Publication date: 1995-07-04
Inventor(s): SAKUMA YOSHIKI (JP)
Applicant(s): FUJITSU LTD (JP)
Requested Patent: ☐ JP6132236
Application Number: US19930137765 19931019
Priority Number(s): JP19920282005 19921020
IPC Classification: C30B25/16
EC Classification: H01L21/20B6B4
EC Classification: H01L21/20B6B4
Equivalents: ☐ FR2697108, JP3137767B2

Abstract

A deposition method of a compound semiconductor forming a semiconductor device comprises the steps of; covering the surface of a compound semiconductor containing a V group element with a III group element with a thickness of one or more monolayers; and forming a second compound semiconductor containing a V group element different from said V group element on said III group element while utilizing said III group element as a protective film for preventing the desorption of said V group element.